

Transistor		Transistor	
Elektrische Eigenschaften		Electrical properties	
Höchstzulässige Werte		Maximum rated values	
V_{CES}		1200	V
I_C		800	A
I_{CRM}	$t_p = 1 \text{ ms}$	1600	A
P_{tot}	$t_C = 25^\circ\text{C}$	6250	W
V_{GE}		20	V
V_{EG}		20	V

Charakteristische Werte		Characteristic values	
$V_{CE \text{ sat}}$	$i_{CM} = 800 \text{ A}, V_{GE} = 15 \text{ V}, t_{vj} = 25^\circ\text{C}$	typ. 3,0	V
	$i_{CM} = 800 \text{ A}, V_{GE} = 15 \text{ V}, t_{vj} = 125^\circ\text{C}$	max. 3,8	V
$V_{GE} \text{ (th)}$	$V_{CE} = 5 \text{ V}, i_C = 65 \text{ mA}, t_{vj} = 25^\circ\text{C}$	min. 4,5	V
	$V_{CE} = 5 \text{ V}, i_C = 65 \text{ mA}, t_{vj} = 25^\circ\text{C}$	max. 6,5	V
C_{ies}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f_o = 1 \text{ MHz}, t_{vj} = 25^\circ\text{C}$	typ. 130	nF
i_{CES}	$V_{CE} = 1200 \text{ V}, V_{GE} = 0 \text{ V}, t_{vj} = 25^\circ\text{C}$	typ. 5	mA
	$V_{CE} = 1200 \text{ V}, V_{GE} = 0 \text{ V}, t_{vj} = 125^\circ\text{C}$	typ. 20	mA
i_{GES}	$V_{GE} = 20 \text{ V}, t_{vj} = 25^\circ\text{C}$	typ. 40	nA
	$V_{GE} = 20 \text{ V}, t_{vj} = 25^\circ\text{C}$	max. 400	nA
i_{EGS}	$V_{EG} = 20 \text{ V}, t_{vj} = 25^\circ\text{C}$	typ. 40	nA
	$V_{EG} = 20 \text{ V}, t_{vj} = 25^\circ\text{C}$	max. 400	nA
t_{on}	$i_{CM} = 800 \text{ A}, V_{CE} = 600 \text{ V}, V_{LF} = 15 \text{ V}, R_G = 2,4 \Omega, t_{vj} = 25^\circ\text{C}$	typ. 0,7	μs
	$i_{CM} = 800 \text{ A}, V_{CE} = 600 \text{ V}, V_{LF} = 15 \text{ V}, R_G = 2,4 \Omega, t_{vj} = 125^\circ\text{C}$	typ. 0,8	μs
t_s	$i_{CM} = 800 \text{ A}, V_{CE} = 600 \text{ V}, V_{LF} = 15 \text{ V}, V_{LR} = 15 \text{ V}, R_G = 2,4 \Omega, t_{vj} = 25^\circ\text{C}$	typ. 0,9	μs
	$i_{CM} = 800 \text{ A}, V_{CE} = 600 \text{ V}, V_{LF} = 15 \text{ V}, V_{LR} = 15 \text{ V}, R_G = 2,4 \Omega, t_{vj} = 125^\circ\text{C}$	typ. 1,0	μs
t_f	$i_{CM} = 800 \text{ A}, V_{CE} = 600 \text{ V}, V_{LF} = 15 \text{ V}, V_{LR} = 15 \text{ V}, R_G = 2,4 \Omega, t_{vj} = 25^\circ\text{C}$	typ. 0,25	μs
	$i_{CM} = 800 \text{ A}, V_{CE} = 600 \text{ V}, V_{LF} = 15 \text{ V}, V_{LR} = 15 \text{ V}, R_G = 2,4 \Omega, t_{vj} = 125^\circ\text{C}$	typ. 0,30	μs

Bedingungen für den Kurzschlußschutz	Conditions for protection against short circuits
$t_{fg} = 10 \mu\text{s}$	$V_{CC} = 750 \text{ V}$
$V_{LF} = V_{LR} = 15 \text{ V}$	$V_{CEM} = 900 \text{ V}$
$R_G = 2,4 \Omega$	$i_{CMK1} \approx 8000 \text{ A}$
$t_{vj} = 125^\circ\text{C}$	$i_{CMK2} \approx 6000 \text{ A}$

Unabhängig davon gilt bei abweichenden Bedingungen
with regard to other conditions
 $V_{CEM} = V_{CES} - 15nH \times |di_C/dt|$

Thermische Eigenschaften		Thermal properties	
R_{thJC}	DC, pro Baustein / per module	0,02	$^\circ\text{C/W}$
R_{thCK}	pro Baustein / per module	0,01	$^\circ\text{C/W}$
$t_{vj \text{ max}}$			150 $^\circ\text{C}$
$t_{vj \text{ op}}$			- 40 / + 150 $^\circ\text{C}$
t_{stg}			- 40 / + 125 $^\circ\text{C}$

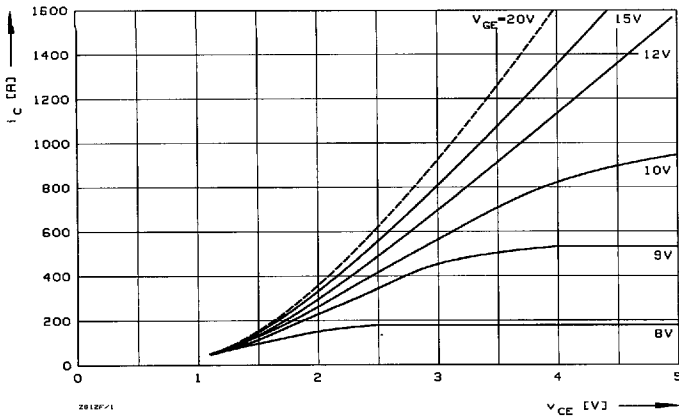
Inversdiode		Inverse diode	
Elektrische Eigenschaften		Electrical properties	
Höchstzulässige Werte		Maximum rated values	
$I_{F(max)}$			800 A
I_{FRM}	$t_p = 1 \text{ ms}$		1600 A

Charakteristische Werte		Characteristic values	
V_F	$i_F = 800 \text{ A}, V_{GE} = 0 \text{ V}, t_{vj} = 25^\circ\text{C}$	typ. 2,5	V
	$i_F = 800 \text{ A}, V_{GE} = 0 \text{ V}, t_{vj} = 125^\circ\text{C}$	max. 2,1	V
I_{RM}	$i_{FM} = 800 \text{ A}, -di_F/dt = 800 \text{ A}/\mu\text{s}$ $V_{EG} = 10 \text{ V}, t_{vj} = 25^\circ\text{C}$	typ. 80	A
	$i_{FM} = 800 \text{ A}, -di_F/dt = 800 \text{ A}/\mu\text{s}$ $V_{EG} = 10 \text{ V}, t_{vj} = 125^\circ\text{C}$	typ. 190	A
Q_r	$i_{FM} = 800 \text{ A}, -di_F/dt = 800 \text{ A}/\mu\text{s}$ $V_{EG} = 10 \text{ V}, t_{vj} = 25^\circ\text{C}$	typ. 12	μAs
	$i_{FM} = 800 \text{ A}, -di_F/dt = 800 \text{ A}/\mu\text{s}$ $V_{EG} = 10 \text{ V}, t_{vj} = 125^\circ\text{C}$	typ. 52	μAs

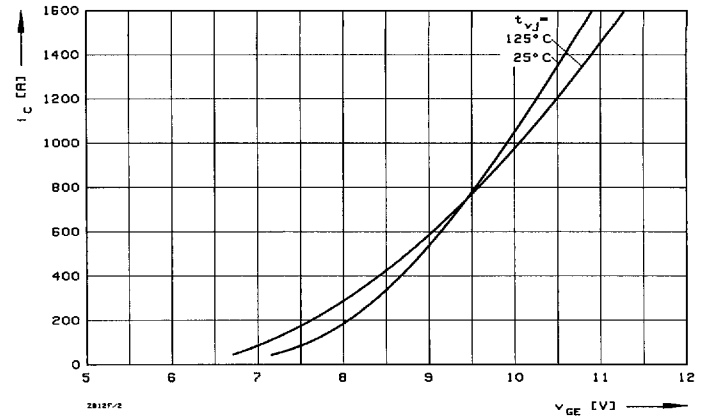
Thermische Eigenschaften		Thermal properties	
R_{thJC}	DC, pro Baustein / per module	0,05	$^\circ\text{C/W}$
R_{thCK}	pro Baustein / per module	0,01	$^\circ\text{C/W}$
$t_{vj \text{ max}}$			150 $^\circ\text{C}$
$t_{vj \text{ op}}$			- 40 / + 125 $^\circ\text{C}$
t_{stg}			- 40 / + 125 $^\circ\text{C}$

Innere Isolation		Internal insulation	
Isoliermaterial: Al_2O_3	Insulating material: Al_2O_3		
V_{ISOL} RMS (f=50 Hz, t=1 min)		3,4	kV

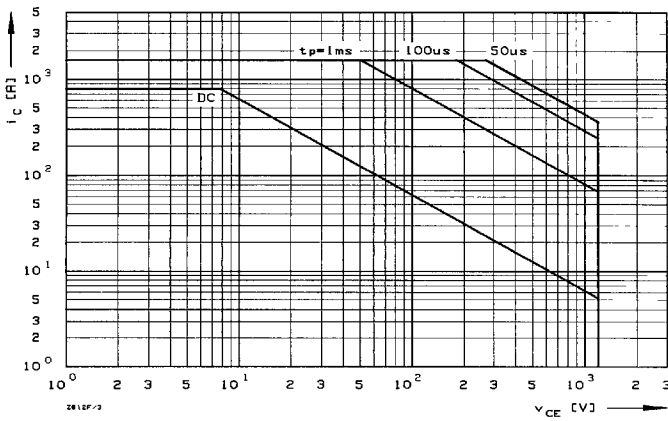
Mechanische Eigenschaften		Mechanical properties	
G			1500 g
M 1			3 Nm
M 2	terminals M 4 / M 8		2 Nm / 8 ... 10 Nm
	Maßbild Seite 185, Nr. 13		outline page 185, no. 13



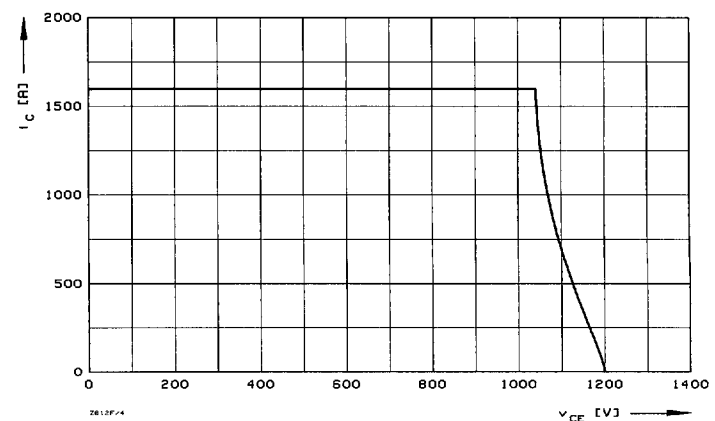
1 Kollektor-Emitter-Spannung im Sättigungsbereich (typisch).
Collector-emitter-voltage in saturation region (typical).
 $t_{vj} = 25^\circ\text{C}$



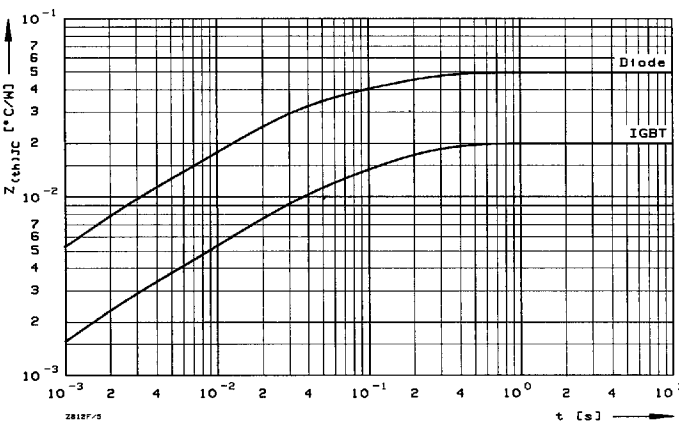
2 Übertragungscharakteristik (typisch).
Transfer characteristic (typical).
 $V_{GE} = 20\text{ V}$



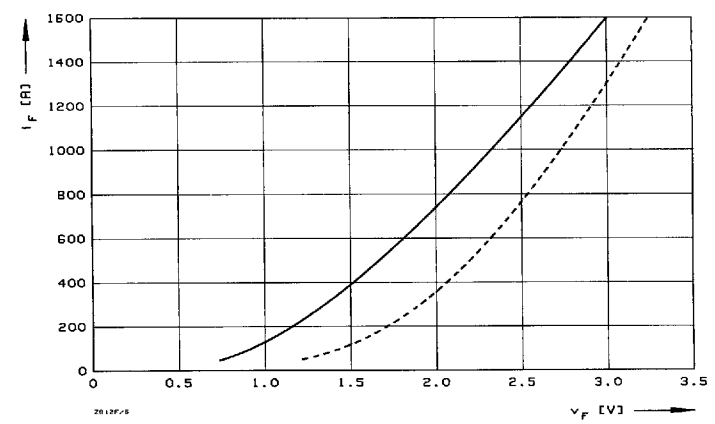
3 Vorwärts-Arbeitsbereich FBSOA (Einzelimpuls, nicht periodisch).
Forward biased safe operating area (single pulse, non repetitive).
 $t_C = 25^\circ\text{C}$



4 Rückwärts-Arbeitsbereich RBSOA
Reverse biased safe operating area.
 $t_{vj} = 125^\circ\text{C}$, $V_{LF} = V_{LR} = 15\text{ V}$, $R_G = 2,4\ \Omega$



5 Transienter innerer Wärmewiderstand je Zweig (DC).
Transient thermal impedance per arm (DC).



6 Durchlaßkennlinie der Inversdiode (typisch).
Forward characteristic of the inverse diode (typical).
--- $t_{vj} = 25^\circ\text{C}$, — $t_{vj} = 125^\circ\text{C}$, $V_{GE} = 0\text{ V}$